VS-HFA50PA60C-N3

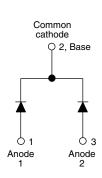
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 25 A



TO-247AC 3L

www.vishay.com



PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 25 A							
V _R	600 V							
V _F at I _F	1.3 V							
t _{rr} typ.	23 ns							
T _J max.	150 °C							
Package	TO-247AC 3L							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA50PA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A per leg continuous current, the VS-HFA50PA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA50PA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _R		600	V						
Maximum continuous forward current	I_	T _C = 100 °C	25							
per device	IF	$1_{\rm C} = 100 {\rm C}$	50	А						
Single pulse forward current	I _{FSM}	t _p = 10 ms	225	~						
Maximum repetitive forward current	I _{FRM}		100							
Maximum power dissinction	Р	T _C = 25 °C	150	W						
Maximum power dissipation	P _D	T _C = 100 °C	60	vv						
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C						

Revision: 11-Oct-2019

Document Number: 94074

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

1



RoHS COMPLIANT HALOGEN

Revision: 11-Oct-2019

2 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Vishay Semiconductors

Document Number: 94074

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	600	-	-				
		I _F = 25 A		-	1.3	1.7	V		
Maximum forward voltage	V _{FM}	I _F = 50 A	See fig. 1	-	1.5	2.0			
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7			
Maximum reverse	1	$V_{R} = V_{R}$ rated	See fig. 2	-	1.5	20			
leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	600	2000	μA		
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	55	100	pF		
Series inductance	Ls	Measured lead to lead 5 mm from p	ackage body	-	12	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 $	A/μs, V _R = 30 V	-	23	-			
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	50	75	ns		
000 hg. 0, 10	t _{rr2}	T _J = 125 °C		-	105	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 25 \text{ A}$ $dI_F/dt = 200 \text{ A}/\mu \text{s}$	-	4.5	10	А		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.0	15	~		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375	nC		
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	420	1200	ne		
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-	A∕µs		
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	λγμs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Junction to case, single leg conducting	P		-	-	0.83					
Junction to case, both legs conducting	R _{thJC}		-	-	0.42	κ/w				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	- r./ vv				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	-					
Waight			-	6.0	-	g				
Weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC 3L		HFA50PA60C						





VS-HFA50PA60C-N3

Vishay Semiconductors

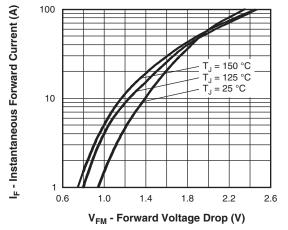


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

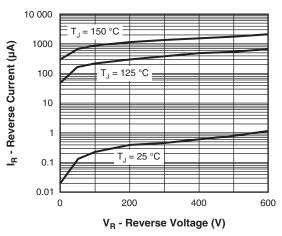


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

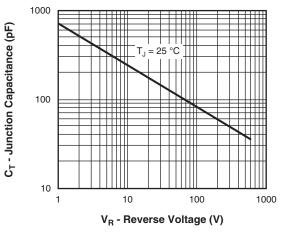


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

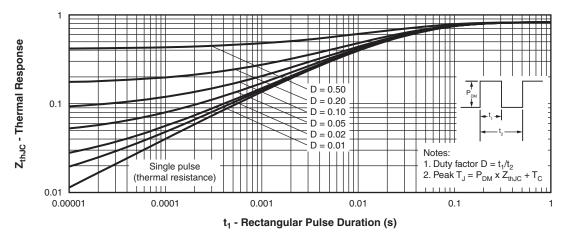


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

 Revision: 11-Oct-2019
 3
 Document Number: 94074

 For technical questions within your region: DiodesAsia@vishay.com, DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



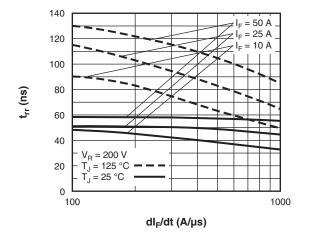


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

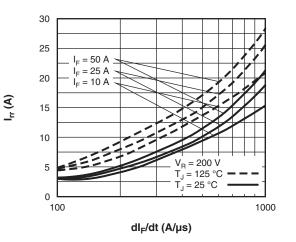


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

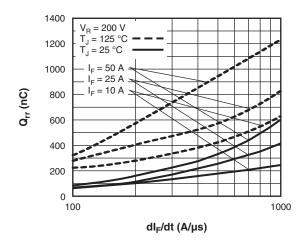


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

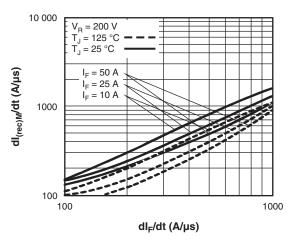


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

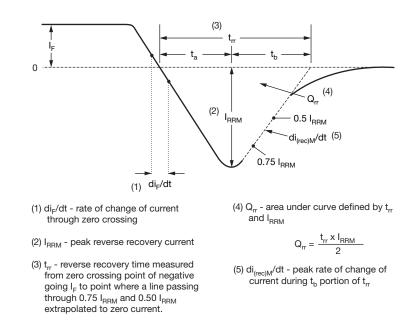


Fig. :	9 - Reverse Recovery Waveform and Definitions	
Revision: 11-Oct-2019	4	Document Number: 94074
For technical questions within your region	n: <u>DiodesAmericas@vishay.com, DiodesAsia@vishay.co</u>	om, <u>DiodesEurope@vishay.com</u>
	GE WITHOUT NOTICE. THE PRODUCTS DESCRIBED CIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com</u>	

VS-HFA50PA60C-N3

Vishay Semiconductors



Vishay Semiconductors



ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	50	PA	60	С	-N3
	1	2	3	4	5	6	7	8
	1 · 2 ·		nay Sen KFRED [©]	niconduo ® family	ctors pro	oduct		
	3 -	Ele	ctron irra	adiated				
	4 · 5 ·			ng (50 = 17AC, 3	-			
	6 - 7 -		0	ng: (60)		
				iguratior				
	8 -	Env	ironmer	ntal digit	:			
		-N3	= halog	en-free,	RoHS-	complia	nt, and	totally I

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA50PA60C-N3	25	500	Antistatic plastic tube					

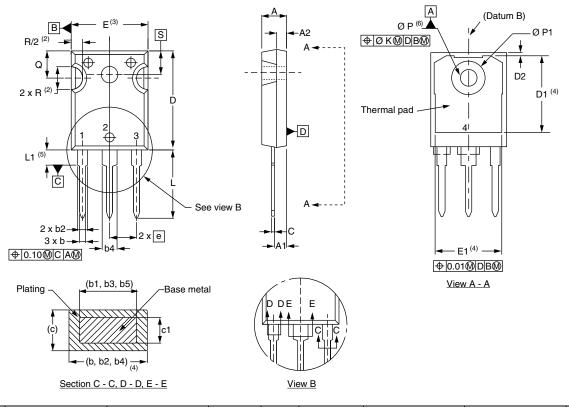
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					



Vishay Semiconductors

TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			Е	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			ØР	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133			Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035			Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033			R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3		S	5.51	BSC	0.217	BSC	
D1	13.08	-	0.515	-	4							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

Revision: 20-Jun-17

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.